

-40V P-CHANNEL Power MOSFET

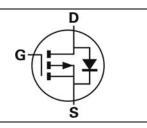
V_{DSS}, -40V

 $R_{DS(ON)}$, $43m\Omega$ (max.) @ VGS=-10V $R_{DS(ON)}$, $70m\Omega$ (max.) @ VGS=-4.5V

I_D, -4.8A



SOP-8



Description

The SGP4038S is the highest performance trench P-ch MOSFETs with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The SGP4038S meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Low On-Resistance
- Low Input Capacitance
- · Low Miller Charge
- Low Input / Output Leakage
- · Pb-free lead plating; RoHS compliant

Applications

- Motor / Body Load Control
- Automotive Systems
- Load Switch
- DC-DC converters and Off-line UPS

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SGP4038S	Halogen-Free	SOP-8	S	Tape & Reel	3,000

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	-40	V
Gate-Source Voltage		V _{GS}	±20	V
Proin Compant Continuous	T _A =25°C		-4.8	А
Drain Current-Continuous	T _A =70°C	I _D	-3.9	А
Drain Current-Pulsed Note 1		I _{DM}	-16	А
Avalanche Current, L=0.1mH		IAS	-25	А
Avalanche Energy, L=0.1mH Note 3		Eas	31.3	mJ
Maximum Power Dissipation	T _A =25°C	D	1.5	W
Maximum Fower Dissipation	T _A =70°C	P _D	0.6	W
Operating Junction Temperature Range		Tu Tstg	-55 to +150	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient	RθJA	Steady State	-	-	85	°C/W
Maximum Junction-to-Case	Rejc	Steady State	-	-	40	°C/W

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Electrical Characteristics (T_J=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =-250μA	-40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-32V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage	Igss	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =-250µA	-1	-	-2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _{DS} =-6A	-	-	43	mΩ
		V _{GS} =-4.5V, I _{DS} =-3A	-	-	70	
Forward Transconductance Note 1	gfs	V _{DS} =-5V, I _D =-3A	-	12	-	S

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	C _{iss}		-	984	-	
Output Capacitance	Coss	V _{DS} =-20V, V _{GS} =0V, f=1MHz	-	105	-	pF
Reverse Transfer Capacitance	Crss		-	78	-	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T _{d(on)}		-	19	-	
Rise Time	tr	V_{DD} =-20V, V_{GS} =-10V, R_{G} =3.3 Ω ,	-	12.6	-	
Turn-Off Delay Time	$T_{d(off)}$	I _D =-3A	-	47.6	-	ns
Fall Time	t _f		-	4.5	-	
Total Gate Charge at 10V	Q_g	V = 20V V = 4.5V	-	8.8	-	
Gate to Source Gate Charge	Qgs	V _{DS} =-20V, V _{GS} =-4.5V, I _D =-3A	-	2.4	-	nC
Gate to Drain "Miller" Charge	Q _{gd}	יער – עו	-	3	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-3A	-	-	-1.2	V
Body Diode Reverse Recovery Time	Is	V _G =V _D =0V, Force Current	-	-	-4.8	Α
Body Diode Reverse Recovery Charge	lsм	VG-VD-UV, FUICE CUITEIIL	-	-	-16	Α

Notes:

- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BJA} is determined by the user's board design. R_{BJA} shown below for single device operation on FR-4 in still air.

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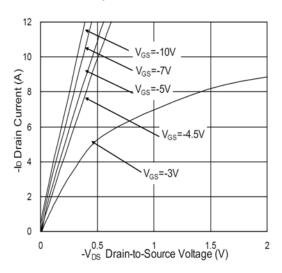
3. The EAS data shows Max. rating. The test condition is V_{DD}=-25V, V_{GS}=-10V, L=0.1mH, I_{AS}=-25A



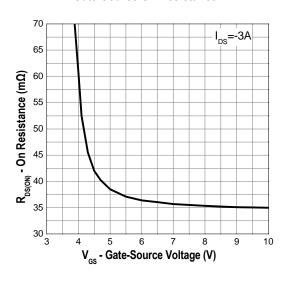
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Typical Operating Characteristics

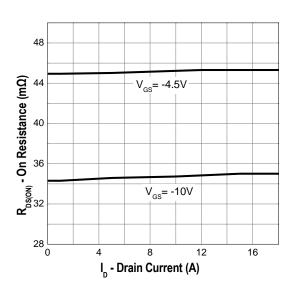
Output Characteristics



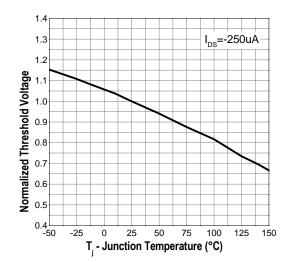
Gate-Source On Resistance



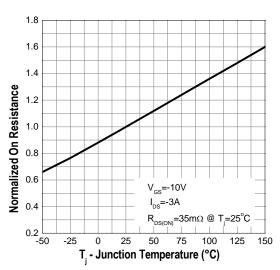
Drain-Source On Resistance



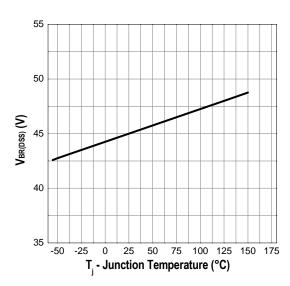
Gate Threshold Voltage



Drain-Source On Resistance



Source-Drain Diode Forward

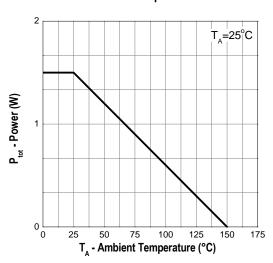




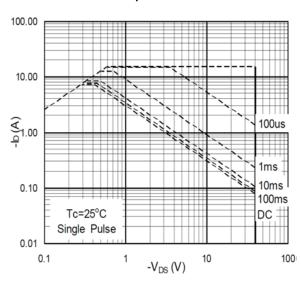
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Typical Operating Characteristics (Cont.)

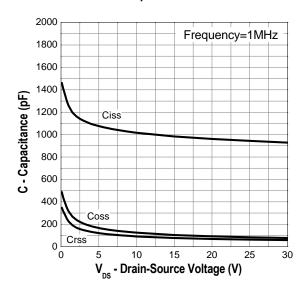
Power Dissipation



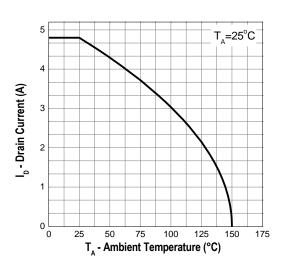
Safe Operation Area



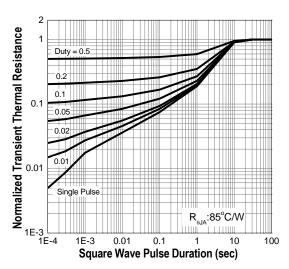
Capacitance



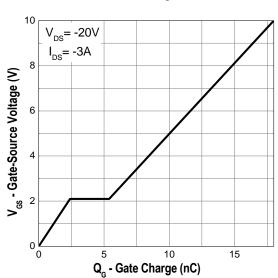
Drain Current



Transient Thermal Impedance



Gate Charge





SGP4038S
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Marking Information

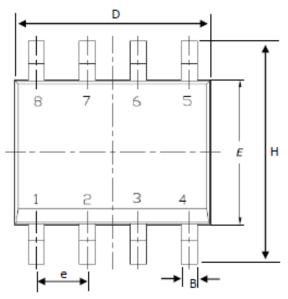
SOP-8 (S)	Marking Rule
SOP-8 (S) Laser Marking SGP4038S YYMMXXX	Line 1 : Device Name SGP4038S Line 2 : Date Code YYMMXXX YY : Year Code MM : Month Code XXX : Serial Number
Diagram	



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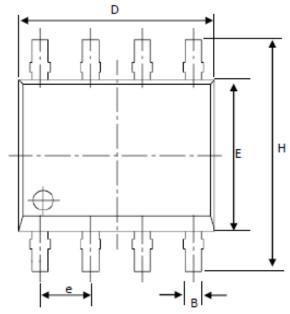
Package of Dimension





Symbol	Min	Nor	Max
Α	1.35	1.55	1.75
A1	0.10	0.18	0.25
В	0.31	0.41	0.51
С	0.17	0.21	0.25
D	4.80	4.90	5.00
E	3.80	3.90	4.00
e	1.27	1.27	1.27
Н	5.80	6.00	6.20
L	0.40	0.84	1.27
α	0.00	4.00	8.00







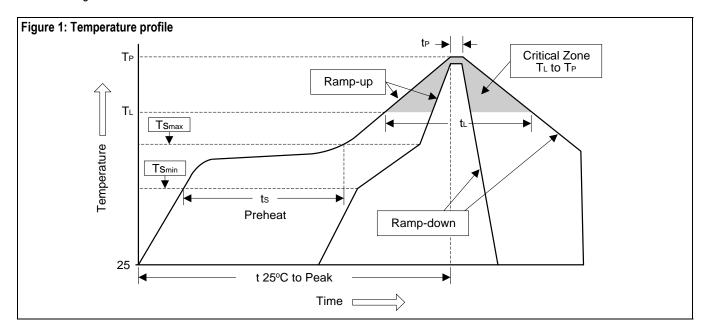
- 1. All dimension are in millimeters.
- 2. Dimension does not include burrs and mold flash/protrusions.



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Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t₂)	10 to 50 sec	20 to 40 Sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec





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